




Air Force Invention No. AFB00670

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On 16 November 2004  
(DATE OF DEPOSIT)

WILLIAM G. AUTON 31,320  
NAME OF APPLICANT, ASSIGNEE, OR REG. REP.

  
16 November 2004  
SIGNATURE DATE

In re application of  
Richard A. Soref  
Application Serial No. 10/722,611  
Filed: 28 November 2003

Examiner: Allan Wilson  
Art Unit: 2815

For: **STRAIN-ENGINEERED DIRECT-GAP  $\text{Ge/Sn}_x\text{Ge}_{1-x}$  HETERODIODE AND  
MULTI-QUANTUM-WELL PHOTODETECTORS, LASERS, EMITTERS AND  
MODULATORS GROWN ON  $\text{Sn}_y\text{Si}_z\text{Ge}_{1-y-z}$ -BUFFERED SILICON**

Honorable Commissioner of Patents  
Alexandria, VA. 22313-1450

#### AMENDMENT

In response to the Office Action of 12 October 2004, please consider the following amendment.